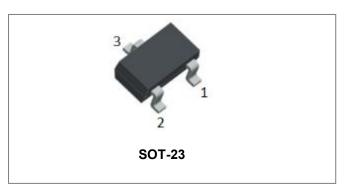




SSTX304S PNP General Purpose Amplifier



Features

- Low saturation Voltage(Transistor) :Vc_{E(sat)}=-0.4V(Max.);Ic=-150mA,I_B=-15mA Fast Reverse Recovery Time(Diode)
- Capable of 350mWatts of Power Dissipation
- Operating and Storage Junction Temperatures: -55℃ to 150℃
- Surface Mount SOT-23 Package
- RoHS compliant / Green EMC
- Collector current: IC=-0.6A

Schematic & Pin Configuration



- 1. EMITTER/CATHODE
- 2. BASE
- 3. COLLECTOR/ANODE

Mechanical Characteristics

- Case: SOT-23, Molded Plastic
- Terminals: Plated leads Solderable per MIL-STD-202,
 - Method 208
- Mounting Position: Any

Maximum Ratings@T_A=25°C unless otherwise specified

TRANSISTOR(Q1)

Characteristic	Symbol	Limits	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	Ic	-0.6	А

DIODE(D1)

Characteristic	Symbol	Limits	Unit
Maximum (peak) Forward Current	I _{FM}	450	mA
Average Forward Current	lo	150	mA
Surge Current (100uS)	I _{FSM}	2	А

COMMON

Characteristic	Symbol	Limits	Unit
Maximum Output (Pin1-Pin3)Voltage	Vo	-60	V
Power Dissipation	Pc	350	mW
Junction Temperature Range	Tj	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

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Electrical Characteristics @T_A=25°C unless otherwise specified

TRANSISTOR(Q1)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =-10μA, I _E =0	-60			V
Emitter-base breakdown voltage	V _{EBO}	I _E =-10μA, I _C =0	-5			V
Collector cutoff current	Ісво	V _{CB} =-50V, I _E =0			-10	nA
		h _{FE(1)} I _C =-0.1mA,V _{CE} =-10V*	75			
	h _{FE}	h _{FE(2)} I _C =-1mA,V _{CE} =-10V*	100			
DC current gain		h _{FE(3)} I _C =-10mA,V _{CE} =-10V*	100			
_		h _{FE(4)} I _C =-150mA,V _{CE} =-10V*	100		300	
		h _{FE(5)} I _C =-500mA,V _{CE} =-10V*	50			
Collector emitter acturation voltage	1/	I _C =-150mA,I _B =-15mA*			-0.4	V
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA,I _B =-50mA*			-1.6	V
Page emitter esturation caltage	1/	I _C =-150mA,I _B =-15mA*			-1.3	V
Base-emitter saturation soltage	$V_{BE(sat)}$	I _C =-500mA,I _B =-50mA*			-2.6	V
Input Capacitance	C _{ib}	V _{EB} =-2V,I _C =0,f=1.0MHZ		17.5		pF

 $^{^{\}star}\,$ Measured under pulsed conditions, Pulse width < 300 $\mu s,\,$ duty cycle < 2%

DIODE(D1)

Characteristics	Symbol	Condition	Min.	Тур.	Max.	Units
Forward Voltage Drop	V_{F1}	I _F =1mA		0.60		
		I _F =10mA		0.72		V
		I _F =100mA		0.90	1.2	

COMMON

Characteristics	Symbol	Condition	Min.	Тур.	Max.	Units
Output Voltage	Vo	I _O =-1mA, I _B =0	-60			V
Output Leakage Current	lo(off)	V _O =-30V, V _{EB} =-0.5V			-0.5	uA
Output Capacitance	C _{Ob}	V _R =-10V,I _E =0,f=1MHZ		8.5		pF

Ordering Information

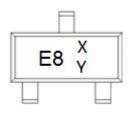
Device	Package	Package Shipping		Emboss pitch	
SSTX304S	SOT-23	3000 pcs / reel	8mm	4mm	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.





Marking Diagram

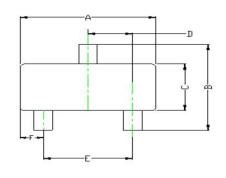


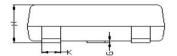
Where XY is date code

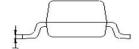
E8 = Marking code X = Month code Y = Lot code

Х	А	В	С	D	E	F	G	Н	J	К	L	М
Month code	January	February	March	April	May	June	July	August	September	October	November	December
Y Lot code	0	1	2	3	4	5	6	7	8	9	-	-

Mechanical Dimensions SOT-23







OVMDOL	Millimeters					
SYMBOL	MIN.	MAX.				
Α	2.800	3.040				
В	2.100	2.640				
С	1.200	1.400				
D	0.890	1.030				
Е	1.780	2.050				
F	0.450	0.600				
G	0.013	0.100				
Н	0.900	1.110				
J	0.090	0.180				
K	0.370	0.510				

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